

1999, which issued on May 22, 2001 as U.S. Patent No. 6,236,104, and U.S. application Serial Number 09/737,715 filed on December 15, 2000.

IN THE ABSTRACT:

Please replace the text in the abstract beginning on page 63, line 1 with the following rewritten text:

The present invention relates to a process for the preparation of a silicon on insulator wafer. The process includes implanting oxygen into a single crystal silicon wafer which is substantially free of agglomerated vacancy-type defects. The present invention further relates to a process for the preparation of a silicon on insulator wafer wherein oxygen is implanted into a single crystal silicon wafer having an axially symmetric region in which there is a predominant intrinsic point defect which is substantially free of agglomerated intrinsic point defects. Additionally, the present invention relates to a silicon on insulator ("SOI") structure in which the device layer and the handle wafer each have an axially symmetric region which is substantially free of agglomerated intrinsic point defects. Additionally, the present invention is directed to such a SOI structure in which the handle wafer is capable of forming an ideal, non-uniform depth distribution of oxygen precipitates upon being subjected to the heat treatment cycles of essentially any arbitrary electronic device manufacturing process.